# HVM132WK
# Silicon Epitaxial Planar Pin Diode for Antenna Switching

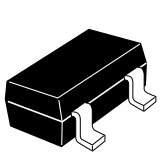
HITACHI

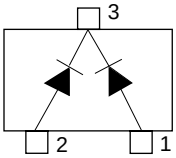
Rev. 2
Jan. 1996

## Features

- Low capacitance.(C=0.5pF max)
- Low forward resistance. ($r_f$=2.0Ω max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

## Outline






(Top View)

1 Anode
2 Anode
3 Cathode

## Ordering Information

| Type No. | Laser Mark | Package Code |
|---|---|---|
| HVM132WK | P4 | MPAK |

## Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Value | Unit |
|---|---|---|---|
| Peak reverse voltage | $V_{RM}$ | 65 | V |
| Reverse voltage | $V_R$ | 60 | V |
| Forward current | $I_F$ * | 100 | mA |
| Power dissipation | $P_d$ * | 150 | mW |
| Junction temperature | $T_j$ | 125 | °C |
| Storage temperature | $T_{stg}$ | -55 to +125 | °C |

* Two device total

## Electrical Characteristics (Ta = 25°C) *

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| Forward voltage | $V_F$ | — | — | 1.0 | V | $I_F$ = 10 mA |
| Reverse current | $I_R$ | — | — | 0.1 | µA | $V_R$ = 60 V |
| Capacitance | C | — | — | 0.5 | pF | $V_R$ = 1 V , f = 1 MHz |
| Forward resistance | $r_f$ | — | — | 2.0 | Ω | $I_F$ = 10 mA, f = 100 MHz |

* Do not guarantee electrical characteristics when forward bias between (1) - (3) or (2) - (3) and reverse bias between (2) - (3) or (1) - (3) at the same time and vice versa.

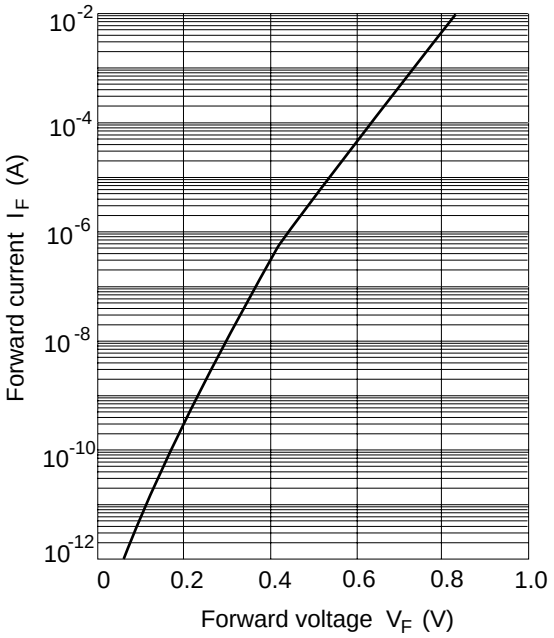



**Fig.1 Forward current Vs. Forward voltage**

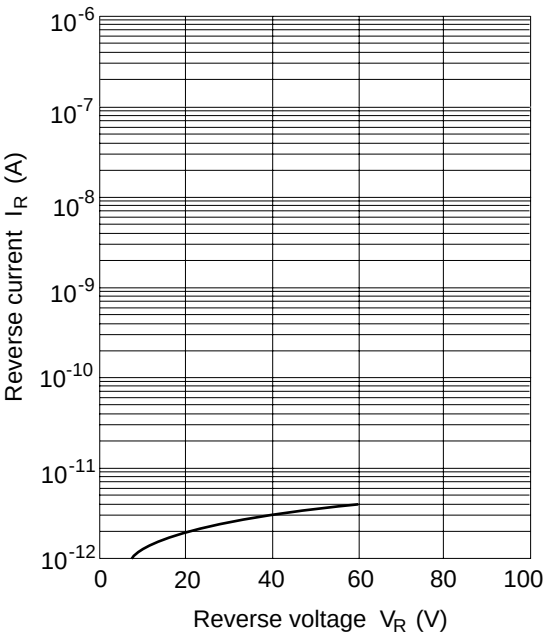



**Fig.2 Reverse current Vs. Reverse voltage**

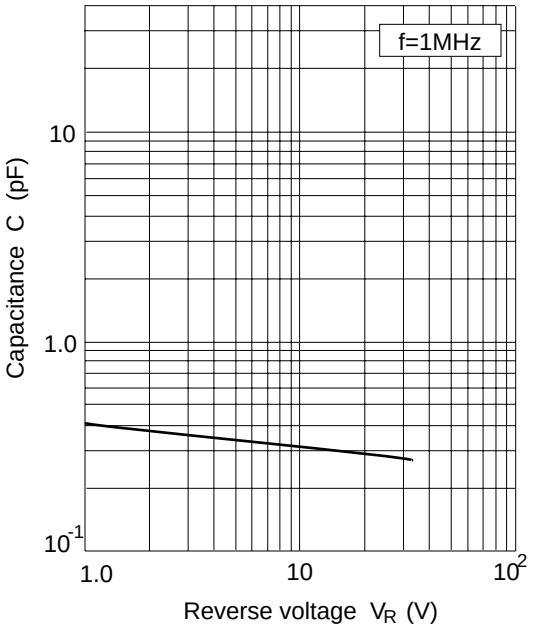



**Fig.3 Capacitance Vs. Reverse voltage**

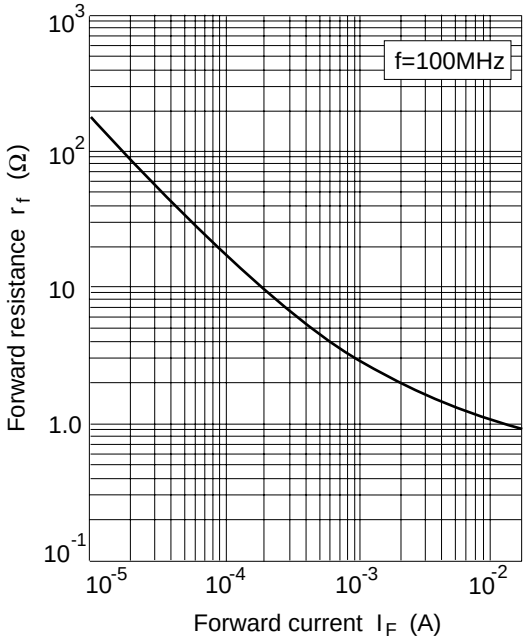
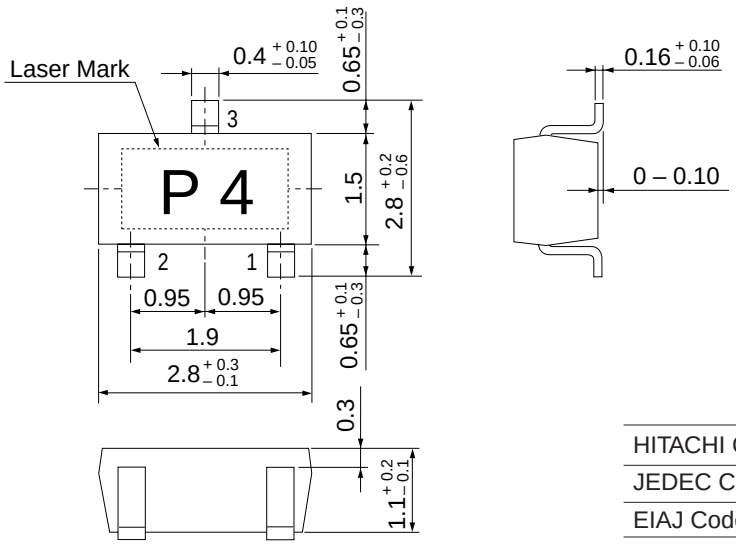



**Fig.4 Forward resistance Vs. Forward current**

## Package Dimensions

Unit: mm




1 Anode
2 Anode
3 Cathode

| | |
|---|---|
| HITACHI Code | MPAK(1) |
| JEDEC Code | — |
| EIAJ Code | SC-59A |
| Weight (g) | 0.011 |